

isc Silicon Darlington NPN Power Transistor

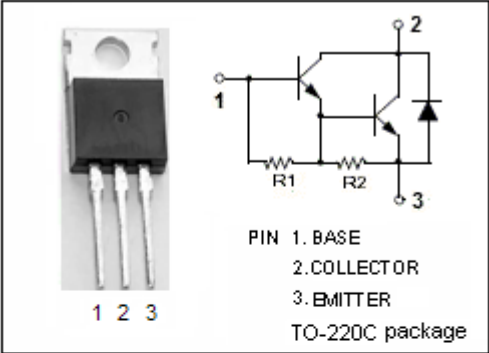
BU522

DESCRIPTION

- High Voltage
- Low Collector Saturation Voltage-
: $V_{CE(sat)} = 2.5V @ I_C = 4A$

APPLICATIONS

- Designed for use in ignition circuit.

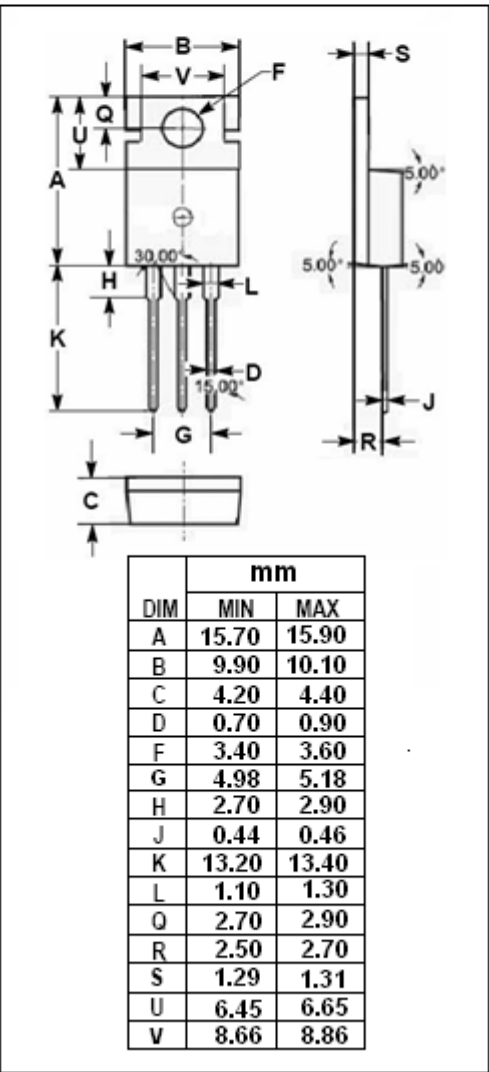


ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CER(SUS)}$	Collector-Emitter Voltage	350	V
V_{CER}	Collector-Emitter Voltage	375	V
V_{CBO}	Collector-Base Voltage	400	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	7	A
I_B	Base Current	2	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}C$	75	W
T_j	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.67	$^{\circ}C/W$



isc Silicon Darlington NPN Power Transistor**BU522****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CER(SUS)}	Collector-Emitter Sustaining Voltage	I _C = 1.0A; R _{BE} = 270 Ω	350			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 4A; I _B = 80mA			2.5	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 4A; I _B = 80mA			2.5	V
I _{CER}	Collector Cutoff Current	V _{CR} = 350V; R _{BE} = 270 Ω			1.0	mA
I _{CBO}	Collector Cutoff Current	V _{CB} = 400V; I _E = 0			1.0	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0			40	mA
h _{FE}	DC Current Gain	I _C = 2.5A; V _{CE} = 5V	250			
f _T	Current-Gain—Bandwidth Product	I _C = 0.3A; V _{CE} = 5V		7.5		MHz
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = 10V; f _{test} = 0.1MHz		150		pF